

Man Young Sung

List of Publications by Year in descending order

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57
papers

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1307594

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docs citations

57
times ranked

230
citing authors

#	ARTICLE	IF	CITATIONS
1	Investigation of the layout and optical proximity correction effects to control the trench etching process on 4H-SiC. <i>Electronic Materials Letters</i> , 2017, 13, 368-372.	2.2	3
2	Unbalanced Layout Method for the 4H-SiC JBS Diode Offering Improved Tradeoff between Leakage Current and ON-Resistance. <i>IEEE Electron Device Letters</i> , 2016, 37, 1045-1047.	3.9	7
3	67-3: Bottom-Gate ELA Poly-Si TFT for High-Resolution AMOLED Mobile Displays. <i>Digest of Technical Papers SID International Symposium</i> , 2016, 47, 923-926.	0.3	10
4	Post-annealing processes to improve inhomogeneity of Schottky barrier height in Ti/Al 4H-SiC Schottky barrier diode. <i>Microelectronic Engineering</i> , 2016, 154, 69-73.	2.4	39
5	Improving Current Density of 4H-SiC Junction Barrier Schottky Diode with Wide Trench Etching. <i>Journal of Nanoscience and Nanotechnology</i> , 2016, 16, 11686-11691.	0.9	2
6	An Analog Front-End IC Design for 320 \times 240 Microbolometer Array Applications. <i>IEEE Transactions on Circuits and Systems II: Express Briefs</i> , 2015, 62, 1048-1052.	3.0	4
7	On-chip stacked punchthrough diode design for 900V power MOSFET gate ESD protection. , 2014, , .		0
8	Enhancement of On-Resistance Characteristics Using Charge Balance Analysis Modulation in a Trench Filling Super Junction MOSFET. <i>Journal of Electrical Engineering and Technology</i> , 2014, 9, 843-847.	2.0	3
9	All digital on-chip temperature sensor using dual ring oscillators. , 2013, , .		3
10	Dual Field Communication Scheme for UHF (860-960 MHz) Gen2 RFID Chip. <i>Integrated Ferroelectrics</i> , 2011, 125, 1-10.	0.7	1
11	Liquid Lens Module with Wide Field-of-View and Variable Focal Length. <i>Electronic Materials Letters</i> , 2010, 6, 141-144.	2.2	4
12	High performance read-out IC design for IR image sensor applications. <i>Analog Integrated Circuits and Signal Processing</i> , 2010, 64, 147-152.	1.4	5
13	Metal-ferroelectric-metal capacitor based persistent memory for electronic product code class-1 generation-2 uhf passive radio-frequency identification tag. <i>Journal of Applied Physics</i> , 2009, 105, 061628.	2.5	1
14	FLOATING-BASE BJT TYPE ESD DEVICE FOR RFID CHIP. <i>Integrated Ferroelectrics</i> , 2009, 105, 45-52.	0.7	1
15	A novel trench IGBT with a rectangular oxide beneath the trench gate. , 2009, , .		3
16	A Novel Trench IGBT With a Deep P^+ Layer Beneath the Trench Emitter. <i>IEEE Electron Device Letters</i> , 2009, 30, 82-84.	3.9	16
17	Design of field limiting ring employing trench structure for high power devices. <i>IEICE Electronics Express</i> , 2009, 6, 1621-1625.	0.8	2
18	A Novel Trench IGBT With a Deep P^+ Layer Beneath the Trench Emitter. <i>IEEE Electron Device Letters</i> , 2009, , .	3.9	0

#	ARTICLE	IF	CITATIONS
19	A New CMOS Read-out IC for Uncooled Microbolometer Infrared Image Sensor. Journal of Infrared, Millimeter and Terahertz Waves, 2008, 29, 953-965.	0.6	6
20	Effects of excess Sb on crystallization of Γ -phase SbTe binary thin films. Physica Status Solidi (A) Applications and Materials Science, 2008, 205, 1636-1640.	1.8	24
21	Influences of partial melting and overheating on amorphization of $\text{Ge}_{20}\text{Sb}_{20}\text{Te}_{50}$ during the reset process. Physica Status Solidi (A) Applications and Materials Science, 2008, 205, 2657-2661.	1.8	0
22	Shielding region effects on a trench gate IGBT. Microelectronics Journal, 2008, 39, 57-62.	2.0	17
23	Use of the p-floating shielding layer for improving electric field concentration of the recessed gate. , 2008, , .		1
24	A new edge termination technique to improve voltage blocking capability and reliability of field limiting ring for power devices. , 2008, , .		6
25	CRYPTO BASED EPC C1G2 UHF (860 MHz~960 MHz) PASSIVE RFID TAG CHIP. Integrated Ferroelectrics, 2008, 100, 216-227.	0.7	0
26	A pre-emphasis output buffer control scheme for a GDDR3 SDRAM interface. IEICE Electronics Express, 2008, 5, 446-450.	0.8	1
27	Observation of hexagonal nuclei in the once melt-quenched $\text{Ge}_2\text{Sb}_2\text{Te}_5$ phase change contact dimensions. Applied Physics Letters, 2007, 91, 083508.	3.3	6
28	A novel current driving method using organic TFT pixel circuit for active-matrix OLED. , 2007, , .		2
29	Novel Process to Improve Defect Problems for Thermal Nanoimprint Lithography. IEEE Transactions on Semiconductor Manufacturing, 2007, 20, 13-19.	1.7	8
30	An improvement of the breakdown voltage characteristic of trench gate IGBTs by using a shielding layer. , 2007, , .		2
31	Design of an organic TFT pixel electrode circuit with enhanced current programming method for active-matrix OLED displays. , 2007, , .		1
32	The effect of a shielding layer on breakdown voltage in a trench gate IGBT. , 2007, , .		14
33	Current Insertion Transient Response for Measuring Phase Margin in Negative Feedback System. , 2007, , .		0
34	A New Organic Thin-Film Transistor Based Current-Driving Pixel Circuit for Active-Matrix Organic Light-Emitting Displays. , 2007, , .		4
35	A CMOS Readout IC Design for Uncooled Infrared Bolometer Image Sensor Application. , 2006, , .		4
36	Deposition of LiNbO_3 thin films for selective etching. Journal of Electroceramics, 2006, 17, 933-935.	2.0	1

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37	A DUAL-GATE CELL (DGC) FeRAM WITH NDRO AND RANDOM ACCESS SCHEME FOR NANOSCALE AND TERABIT NON-VOLATILE MEMORY. Integrated Ferroelectrics, 2006, 81, 141-148.	0.7	0
38	Design of readout IC for uncooled infrared bolometer sensor using bias offset correction technique. , 2005, , .		0
39	ESD protection circuit with an improved ESD capability for input or output circuit protection. , 2005, , .		0
40	The characteristics of joints with Indium-silver alloy using diffusion soldering method. Materials Research Society Symposia Proceedings, 2004, 817, 13.	0.1	0
41	The Fabrication and Experimental Results of a New Lateral Trench Electrode IGBT with a p+ Diverter. Journal of Computational Electronics, 2003, 2, 21-28.	2.5	0
42	Semiconductor nanowires surrounded by cylindrical Al ₂ O ₃ shells. Journal of Electronic Materials, 2003, 32, 1344-1348.	2.2	14
43	Photocurrent in a hybrid system of 1-thioglycerol and HgTe quantum dots. Materials Research Society Symposia Proceedings, 2003, 789, 115.	0.1	0
44	Effect of Excimer Laser Annealing on Optical Properties of GaN Films Deposited by R.F. Magnetron Sputtering. Materials Research Society Symposia Proceedings, 2001, 693, 507.	0.1	0
45	A novel lateral trench IGBT employing the p+ diverter having superior forward blocking and latch-up characteristics. , 0, , .		0
46	Simulation of a lateral trench IGBT with p+ diverter having superior electrical characteristics. , 0, , .		0
47	Dual-channel SOI LIGBT with improved latch-up and forward voltage drop characteristics. , 0, , .		0
48	Lateral trench IGBT with effective p/sup +/ diverter having superior electrical characteristics for smart power IC. , 0, , .		0
49	A small sized lateral trench electrode IGBT having improved latch-up and breakdown characteristics for power IC system. , 0, , .		1
50	Electrical characteristics of a new lateral trench electrode IGBT for smart power IC. , 0, , .		0
51	Simulation of a lateral trench IGBT with p/sup +/ diverter for improving latch-up characteristics. , 0, , .		0
52	A novel trench-type LIGBT having superior electrical characteristics. , 0, , .		0
53	A new lateral trench IGBT with p+ diverter having superior electrical characteristics. , 0, , .		3
54	A new EST with dual trench gate electrode (DTG-EST). , 0, , .		0

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55	Bias Offset Correction Technique For Uncooled Infrared Bolometer Sensor Readout IC. , 0, , .		1
56	Effects of Channel Doping Profile on Electrical Characteristics of Impact Ionization MOS. , 0, , .		0
57	ESD Protection Circuit with Separated GGNMOS Segment for Input Protection. , 0, , .		2